

Appl. No. 10/711,376  
Amdt. dated November 29, 2005  
Reply to Office action of August 30, 2005

**REMARKS/ARGUMENTS**

**1. Regarding the Office action, dated 08/30/2005:**

- 5           Claims 7-9 are rejected under 35 U.S.C 102(b) as being anticipated by Bourassa (US Pat. 4658378). Claims 1-6 and 10-13 are rejected under 35 U.S.C 103(a) as being anticipated by Bourassa (US Pat. 4658378) in view of Kim (US Pat. 5780333).

**Response:**

- 10           According to US Pat. 4658378 (column 5, lines 3-14), Bourassa first utilizes an N-type dopant to dope a polysilicon, and utilizes a P-type dopant of equal or greater concentration thereafter to uniformly dope the polysilicon. Next, the resistor is masked and the unmasked portion of the polysilicon is doped with an N-type dopant at a concentration greater than the P-type dopant used in the prior step to form regions with different resistance on the surface of
- 15           the polysilicon. In other words, the method of forming polysilicon resistor disclosed by Bourassa essentially involves three doping processes, in which the step of forming regions with different resistance is achieved by doping the unmasked portion of the polysilicon with the third dopant, thus the N-type dopant.
- 20           In contrast to Bourassa, the claimed invention utilizes a first dopant and a second dopant to dope a polysilicon, and then utilizes a salicide layer to adjust the resistance of the polysilicon resistor. In other words, the process of utilizing the salicide layer to adjust the resistance of the polysilicon resistor is performed while the first dopant and the second dopant are evenly distributed on the polysilicon, which is significantly different from the method
- 25           disclosed by Bourassa of utilizing three doping processes to adjust the resistance of the polysilicon resistor. Additionally, the salicide layer disclosed by Kim is fabricated on a metal oxide semiconductor (MOS), which is significantly different from the claimed

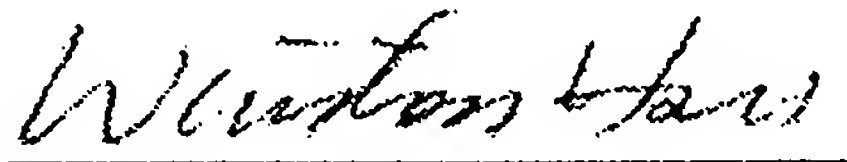
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invention that the salicide layer is fabricated on a polysilicon resistor. Hence, those skilled in the art would find it physically impossible to combine the references in the manner suggested.

5 Applicant respectfully requests that a timely Notice of Allowance be issued in this case.

Sincerely yours,

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20